

N-channel 100V 13.9mΩ standard level MOSFET in D2PAK

21 February 2014

Product data sheet

### 1. General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	68	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13		-	19.4	25	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 13		-	10.8	13.9	mΩ
Dynamic c	haracteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; Fig. 15; Fig. 14		-	17	23.8	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; Fig. 14; Fig. 15		-	59	83	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness						_	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})} \texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D} \texttt{=} 68 \; A; \\ V_{sup} \texttt{\leq} 100 \; V; \; \text{unclamped}; \; R_{GS} \texttt{=} 50 \; \Omega \end{array}$		-	-	127	mJ

[1] Continuous current is limited by package

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UFA
mb	D	mounting base; connected to drain		mbb076 S
			D2PAK (SOT404)	

[1] It is not possible to make connection to pin 2.

# 6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMN013-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404					

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN013-100BS	PSMN013-100BS

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
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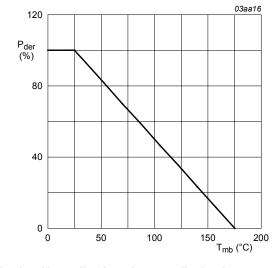
Product data sheet

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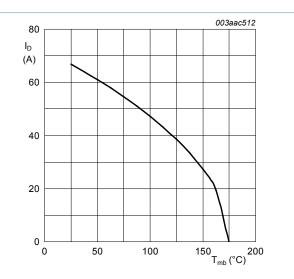
Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	170	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	47	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	68	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	272	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	68	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	272	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 68 A; V <sub>sup</sub> ≤ 100 V; unclamped; R <sub>GS</sub> = 50 Ω		-	127	mJ

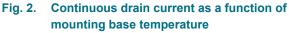
[1] Continuous current is limited by package



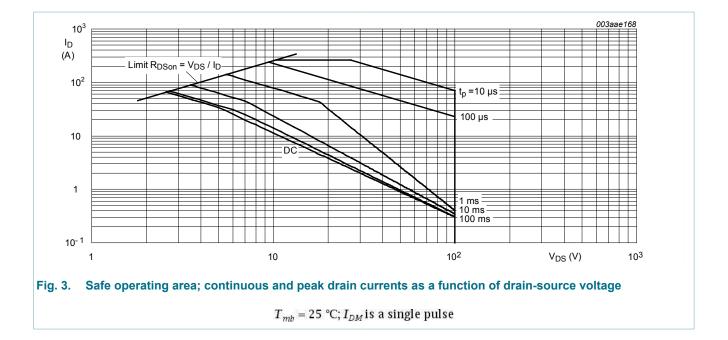


$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



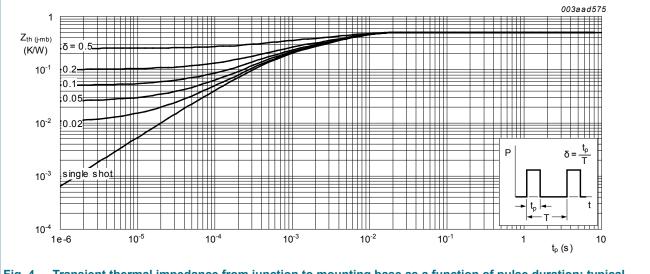


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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	0.5	0.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



# Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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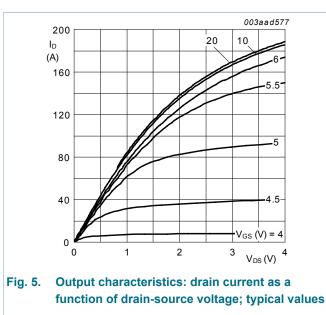
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	octeristics	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 10</u>	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 10	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.06	2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13	-	19.4	25	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	29.5	38.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 13	-	10.8	13.9	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.5	1	2	Ω
Dynamic ch	aracteristics	11				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	59	83	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	47.6	66.7	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	13.8	19.4	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 15; Fig. 14	-	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	4.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	17	23.8	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 50 V; <u>Fig. 15; Fig. 14</u>	-	4.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	3195	4315	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	221	300	pF

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C <sub>rss</sub>	reverse transfer capacitance			-	136	191	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $R_L$ = 2 Ω; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 4.7 Ω; $T_j$ = 25 °C		-	20.7	31.1	ns
t <sub>r</sub>	rise time			-	25	37.5	ns
t <sub>d(off)</sub>	turn-off delay time			-	52.5	78.8	ns
t <sub>f</sub>	fall time			-	24	36	ns
Source-dra	in diode	1	I			1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = 100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V		-	52	68	ns
Q <sub>r</sub>	recovered charge			-	109	142	nC



 $T_j = 25 \,^{\circ}C$ 

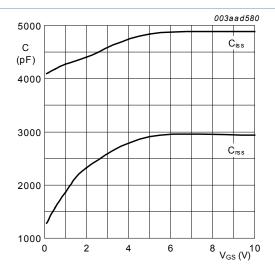
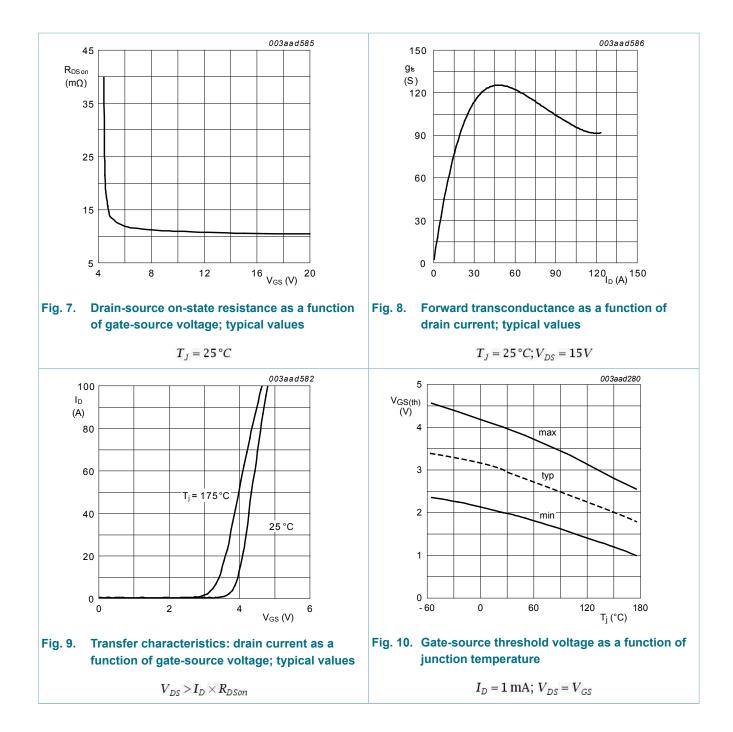


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$ 

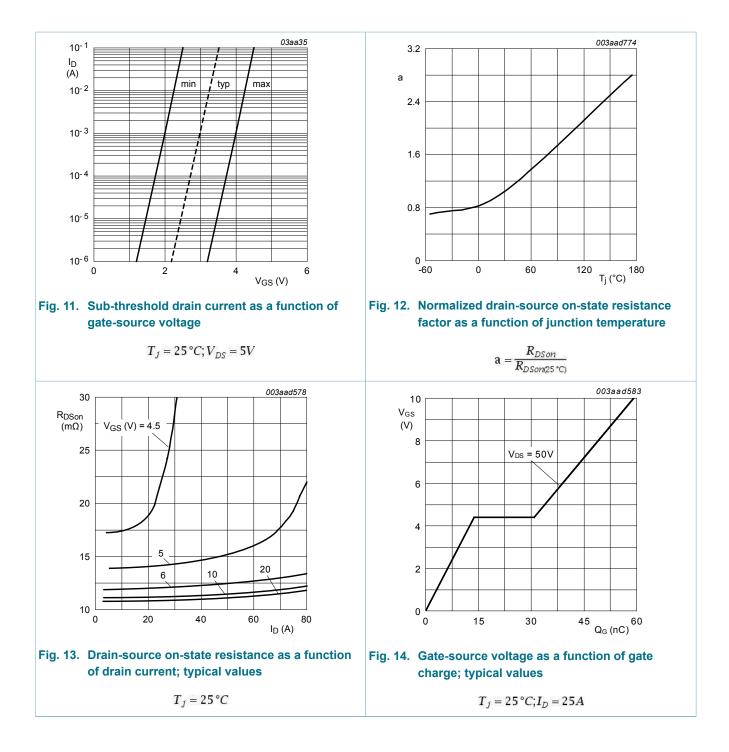
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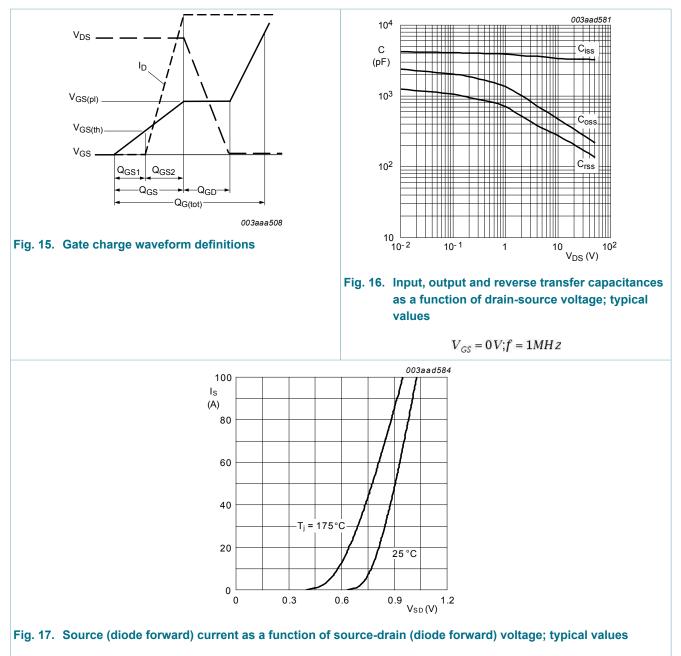


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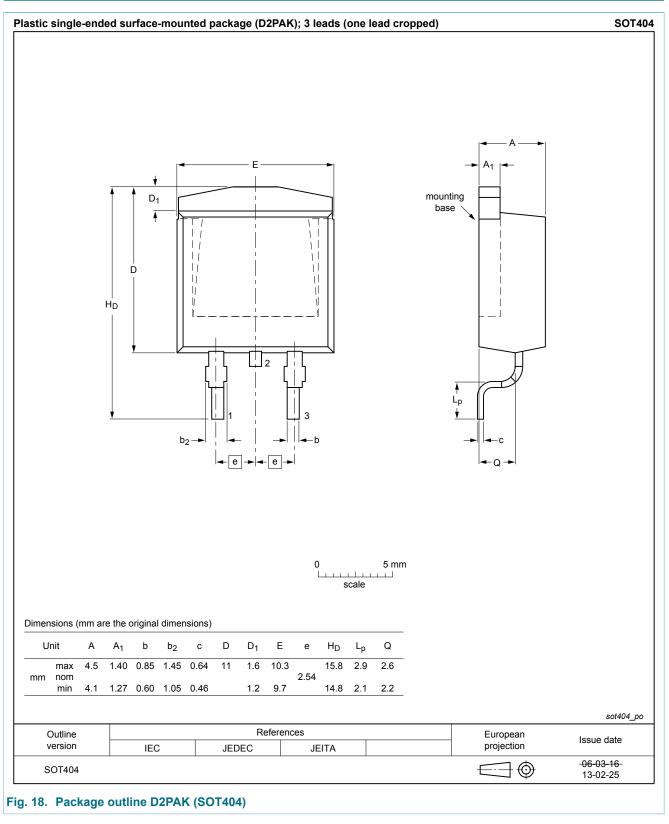
#### N-channel 100V 13.9m $\Omega$ standard level MOSFET in D2PAK



 $V_{GS} = \mathbf{0}V$ 

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### 11. Package outline



#### N-channel 100V 13.9mΩ standard level MOSFET in D2PAK

#### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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